

## S1-1.5

# The Impact of Porosification Upon Luminescence of HVPE Grown GaN and the Influence of the Porous Layer Upon the Quality of the Overgrown GaN Film

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In this paper, we show that the quality of the porous layers produced by photoelectrochemical (PEC) etching of HVPE GaN in oxalic acid is better than that of the initial material, and the quality of GaN films overgrown on porous layers can be improved by adjusting the conditions of PEC etching during the preparation of porous layers. The better quality of the porous layers produced in HVPE material is indicated by the photoluminescence (PL) analysis which shows a higher intensity of the luminescence related to the recombination of free excitons as well as the intensity of the blue luminescence in the porous layers.